

## NPN POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/525

### Devices

**2N6546**

**2N6547**

### Qualified Level

**JAN  
JANTX  
JANTXV**

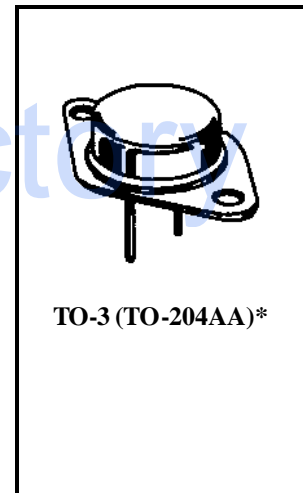
### MAXIMUM RATINGS

Ratings	Symbol	2N6546	2N6547	Units
Collector-Emitter Voltage	$V_{CEO}$	300	400	Vdc
Collector-Base Voltage	$V_{CEX}$	600	850	Vdc
Emitter-Base Voltage	$V_{EBO}$		8	Vdc
Base Current	$I_B$		10	Adc
Collector Current	$I_C$		15	Adc
Total Power Dissipation	$P_T$	@ $T_C = +25^{\circ}C$ <sup>(1)</sup>	175	W
		@ $T_C = +100^{\circ}C$ <sup>(1)</sup>	100	W
Operating & Storage Temperature Range	$T_{op}, T_{stg}$	-65 to +200		$^{\circ}C$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ}C/W$

1) Between  $T_C = +25^{\circ}C$  and  $T_C = +200^{\circ}C$ , linear derating factor (average) = 1.0 W/ $^{\circ}C$



\*See Appendix A for Package Outline

### ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
-----------------	--------	------	------	------

### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 100$ mAdc	2N6546 2N6547	$V_{(BR)CEO}$	300 400	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 600$ Vdc; $V_{BE} = 1.5$ Vdc $V_{CE} = 850$ Vdc; $V_{BE} = 1.5$ Vdc	2N6546 2N6547	$I_{CEX}$	1.0 1.0	mAdc
Emitter-Base Cutoff Current $V_{EB} = 8$ Vdc		$I_{EBO}$	1.0	mAdc

